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(54) Title: FLOWABLE FILM FORMATION AND TREATMENTS

(57) Abstract: Exemplary processing methods may include forming a plasma of a silicon-containing precursor. The methods may include depositing a flowable film on a semiconductor substrate with plasma effluents of the silicon-containing precursor. The semiconductor substrate may define a feature within the semiconductor substrate. The methods may include forming a plasma of a hydrogen-containing precursor within the processing region of the semiconductor processing chamber. A bias power may be applied to the substrate support from a bias power source. The methods may include etching the flowable film from a sidewall of the feature within the semiconductor substrate with plasma effluents of the hydrogen-containing precursor. The methods may include densifying remaining flowable film within the feature defined within the semiconductor substrate with plasma effluents of the hydrogen-containing precursor.

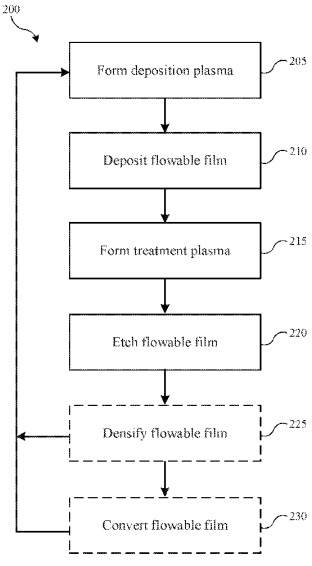



*FIG. 2*

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